Ordering number : ENN7767

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

2SK3747 — High-Voltage, High-Speed Switching Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		1500	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		2	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	P_D		3.0	W
		Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		42	mJ
Avalanche Current *2	I_{AV}		2	A

*1 V_{DD}=99V, L=20mH, I_{AV}=2A

*2 L≤20mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	1500			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=1200V, V_{GS}=0			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}= ±16V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	2.5		3.5	V
Forward Transfer Admittance	|yfs|	V_{DS}=20V, I_D=1A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=1A, V_{GS}=10V		10	13	Ω

Marking : K3747

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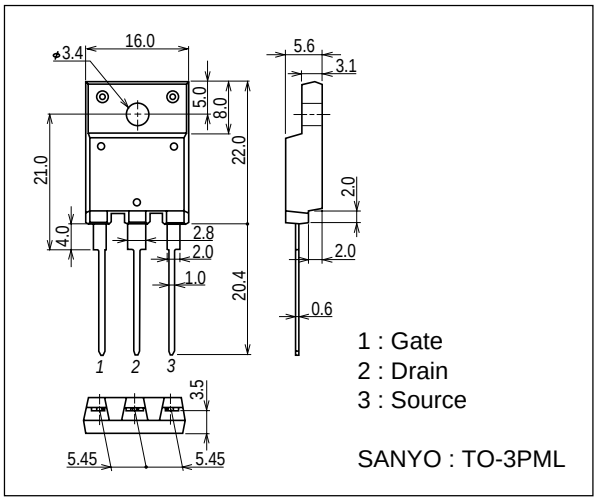
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		400		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		85		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		45		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		12.5		ns
Rise Time	t_{r}	See specified Test Circuit.		30		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		152		ns
Fall Time	t_{f}	See specified Test Circuit.		45		ns
Total Gate Charge	Qg	V_{DS}=200V, V_{GS}=10V, I_{D}=2A		37.5		nC
Gate-to-Source Charge	Qgs	V_{DS}=200V, V_{GS}=10V, I_{D}=2A		2.7		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=200V, V_{GS}=10V, I_{D}=2A		20		nC
Diode Forward Voltage	V_{SD}	I_{S}=2A, V_{GS}=0		0.88	1.2	V

Note) Although the protection diode is contained between gate and source, be careful of handling enough.

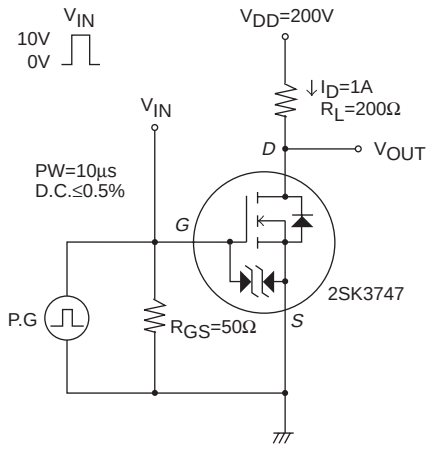
Package Dimensions

unit : mm

2076B



Switching Time Test Circuit



Unclamped Inductive Test Circuit